80V N-Channel MOSFET

Lead Free Package and Finish

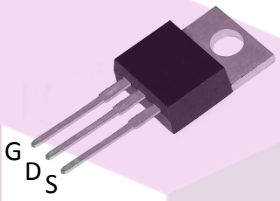
BV_{DSS}	$R_{DS(ON),typ.}$	I_D[2]
80V	4.2mΩ	130A

General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}$=4.2 mΩ@V_{GS}=10V
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

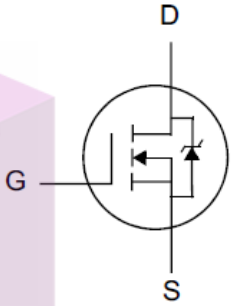
Applications

- High efficiency DC/DC Converters
- Synchronous Rectification
- UPS Inverter



TO-220

Package Not to Scale



Ordering Information

Part Number	Package	Brand
PTP04N08N	TO-220	

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	PTP04N08N	Unit
V_{DSS}	Drain-to-Source Voltage[1]	80	V
V_{GSS}	Gate-to-Source Voltage	±20	
I_D	Continuous Drain Current[2]	130	A
	Continuous Drain Current[3]	80	
$I_{D\ @\ Tc\ =100℃}$	Continuous Drain Current @ Tc=100℃[2]	100	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2,4]	390	
E_{AS}	Single Pulse Avalanche Energy	900	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	300	W
	Derating Factor above 25℃	2.0	W/℃
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 175	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTP04N08N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.5	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	80	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	5	uA	V_{DS}=80V, V_{GS}=0V
		--	--	100		V_{DS}=64V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+20V, V_{DS}=0V
		--	--	-100		V_{GS}=-20V, V_{DS}=0V

ON Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	4.2	6.0	mΩ	V_{GS}=10V, I_D=80A [5]
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250uA
gfs	Forward Transconductance	--	149	--	S	V_{DS}=10V,I_D=80A [5]

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	5300	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MH_Z
C_{rss}	Reverse Transfer Capacitance	--	150	--		
C_{oss}	Output Capacitance	--	420	--		
R_G	Gate Series Resistance	--	1.8	--	Ω	f=1.0MH_Z
Q_g	Total Gate Charge	--	68	--	nC	V_{DD}=40V, I_D=80A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	20	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	15	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	26	--	nS	V_{DD}=40V, I_D=40A, V_{GS}= 10V R_G=10Ω
t_{rise}	Rise Time	--	73	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	88	--		
t_{fall}	Fall Time	--	58	--		

Source-Drain Body Diode Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current[2]	--	--	130	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[2]	--	--	390		
V_{SD}	Diode Forward Voltage	--	--	1.2	V	I_S=80A, V_{GS}=0V
trr	Reverse recovery time	--	58	--	ns	V_{GS}=0V ,I_F=80A, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	154	--	nC	

Note:

[1] T_J=+25℃ to +175℃
[2] Silicon limited current only.
[3].Package limited current
[4] Repetitive rating; pulse width limited by maximum junction temperature.
[5] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

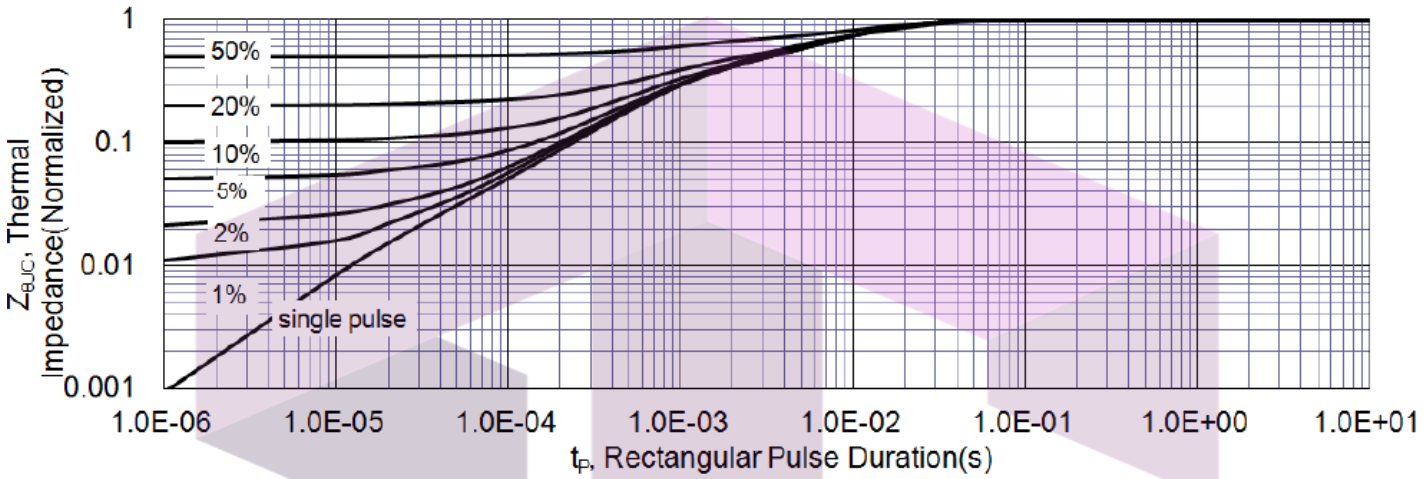


Figure 2. Maximum Power Dissipation vs Case Temperature

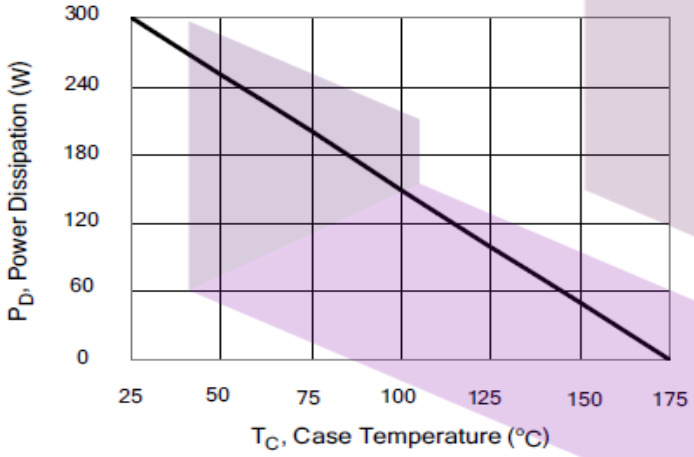


Figure 3 .Maximum Continuous Drain Current vs Case Temperature

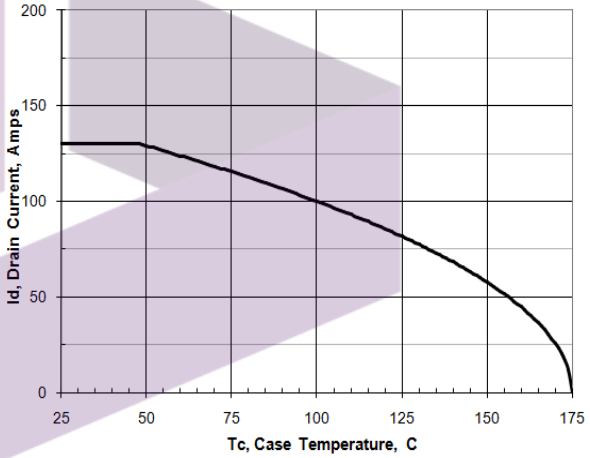


Figure 4. Typical Output Characteristics

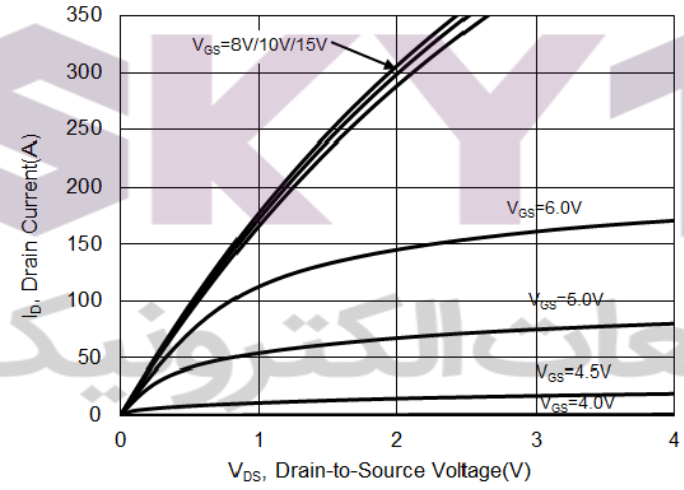
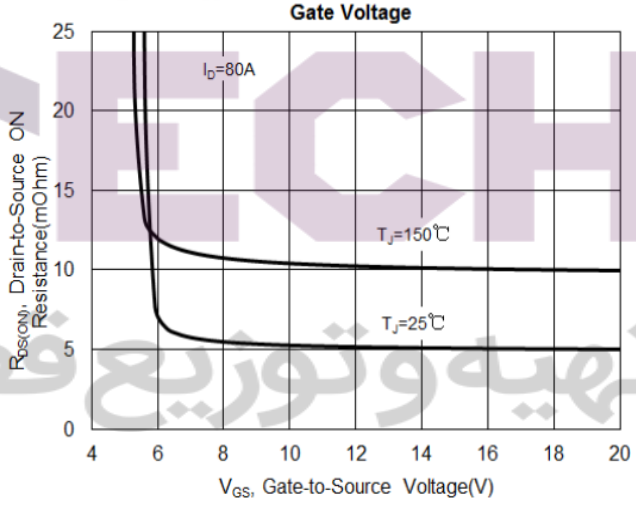


Figure 5. Typical Drain-to-Source ON Resistance vs. Gate Voltage



Typical Characteristics(Cont.)

Figure 6. Peak Current Capability

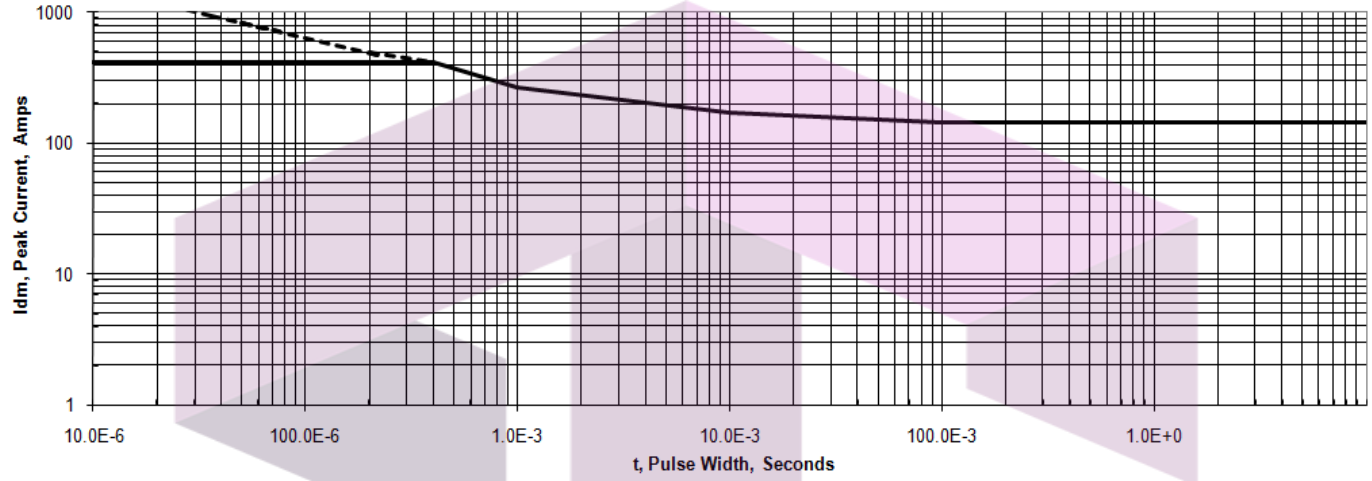


Figure 7. Typical Transfer Characteristics

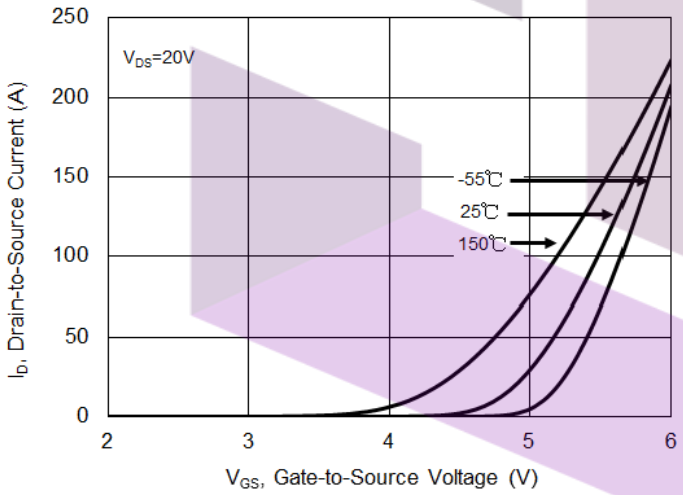


Figure 8. Unclamped Inductive Switching Capability

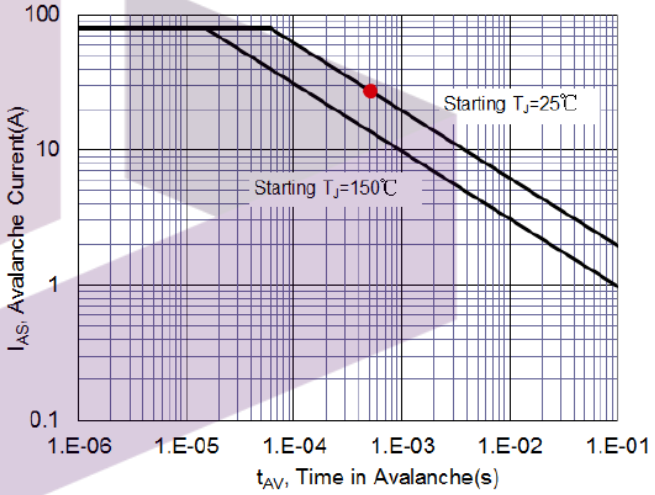


Figure 9. Typical Drain-to-Source ON Resistance

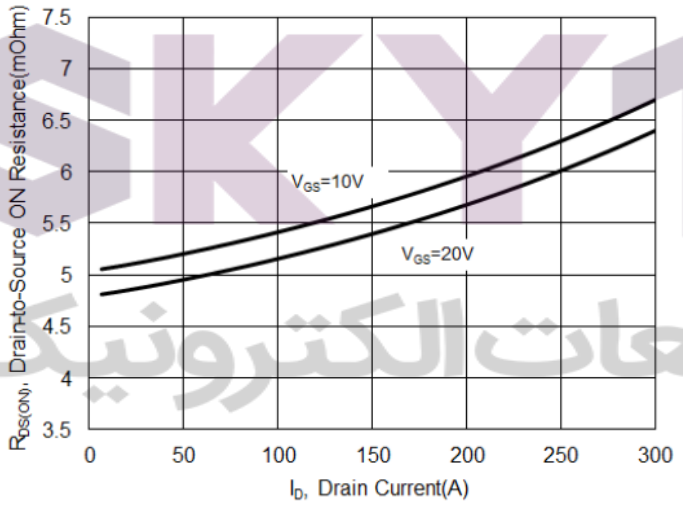
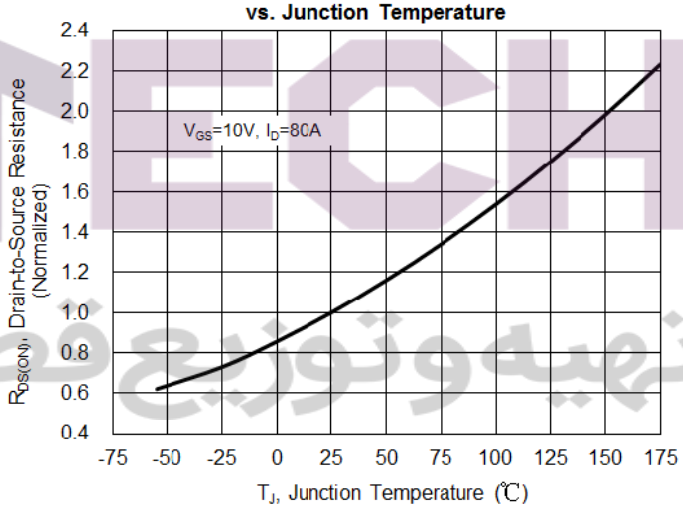


Figure 10. Typical Drain-to-Source On Resistance vs. Junction Temperature



Typical Characteristics(Cont.)

Figure 11.Typical Breakdown Voltage vs. Junction Temperature

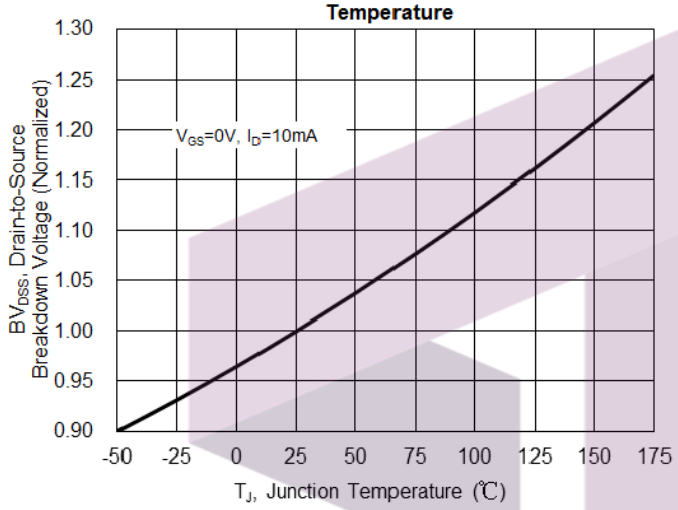


Figure 12.Typical Threshold Voltage vs. Junction Temperature

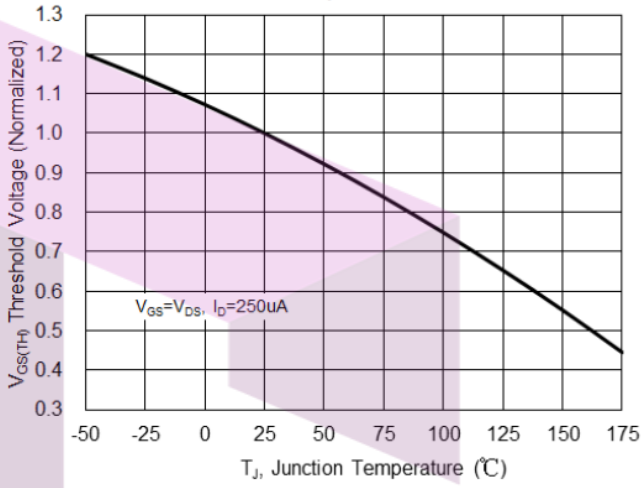


Figure 13 . Maximum Safe Operating Area

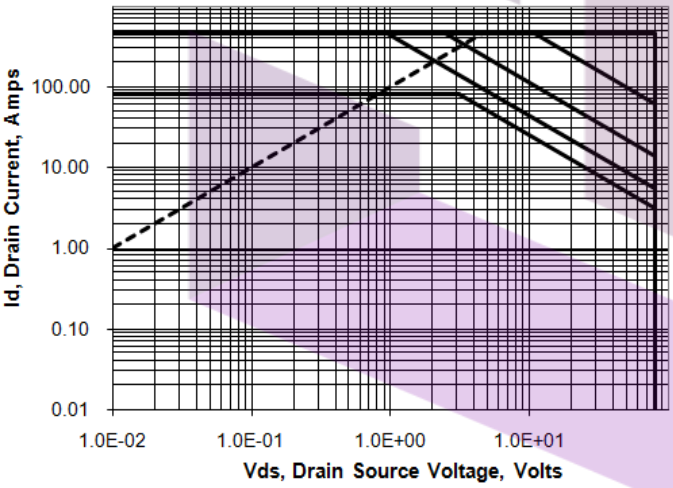


Figure 14. Typical Capacitance vs. Drain-to-Source Voltage

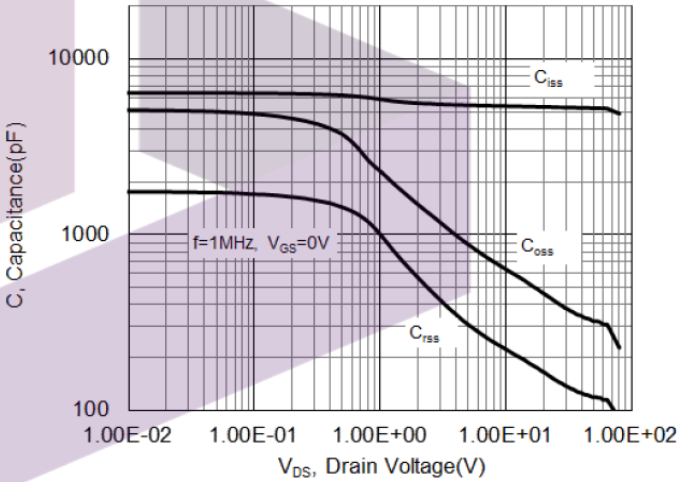


Figure 15. Typical Gate Charge vs. Gate-to-Source Voltage

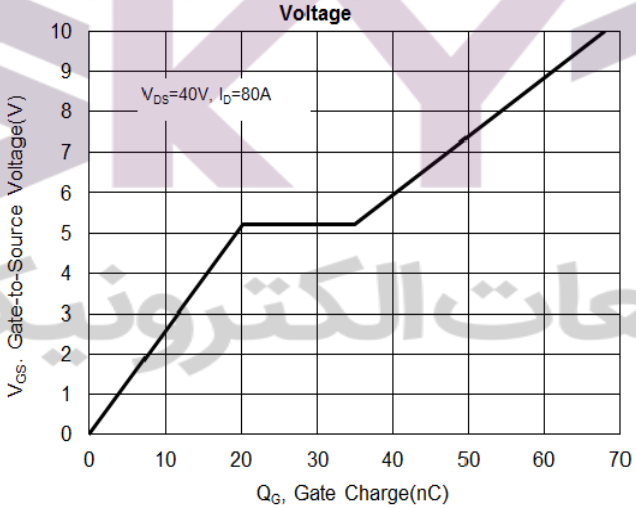
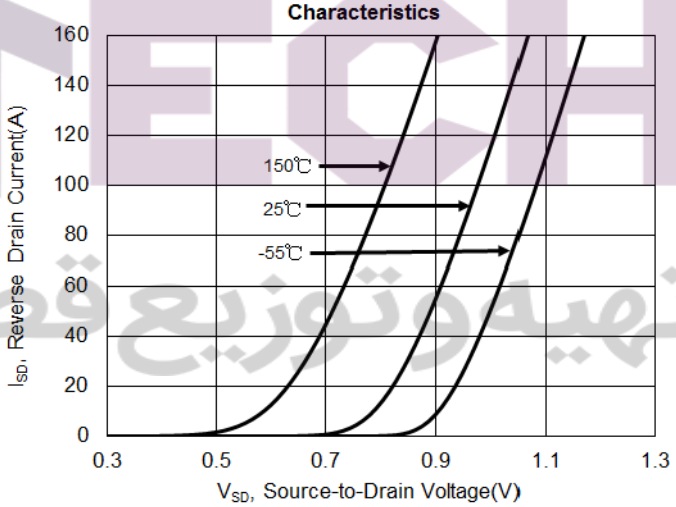


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

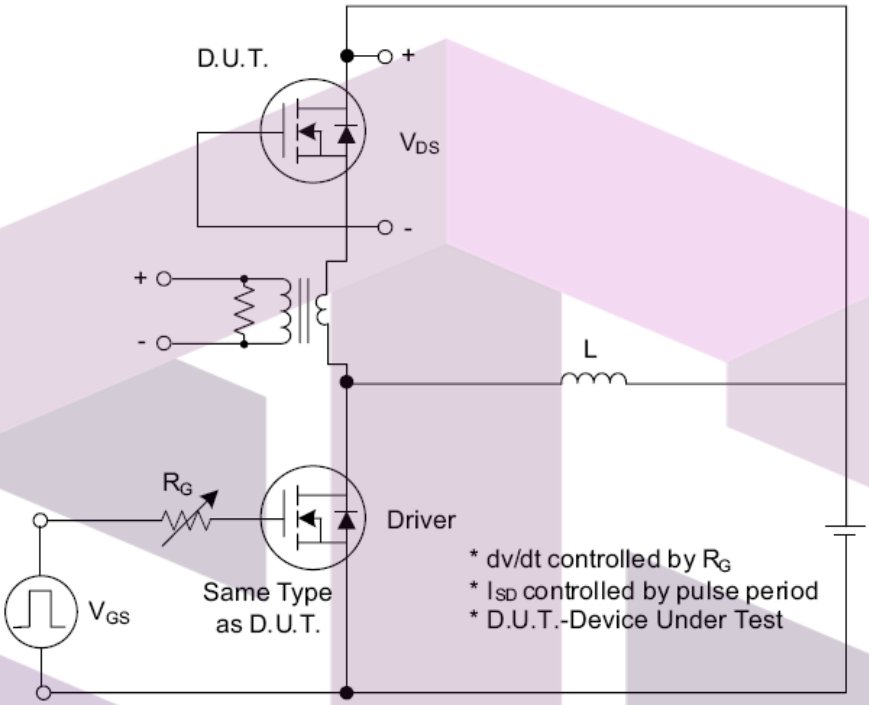


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

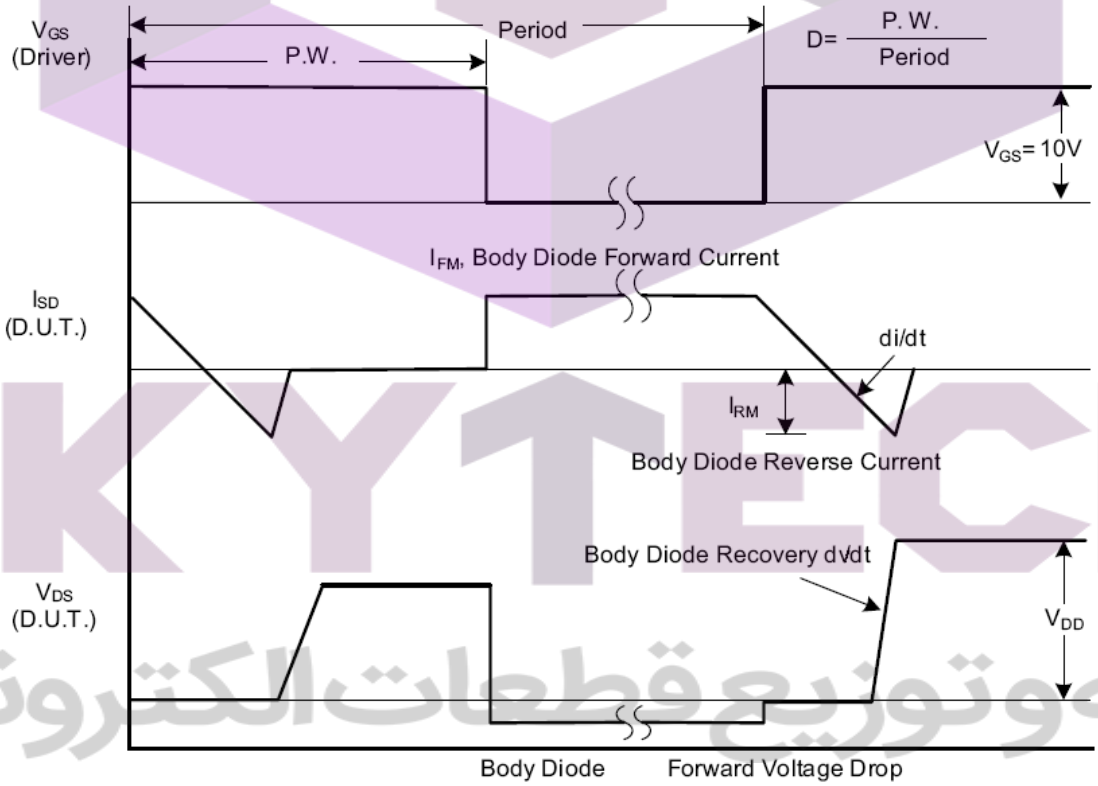


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

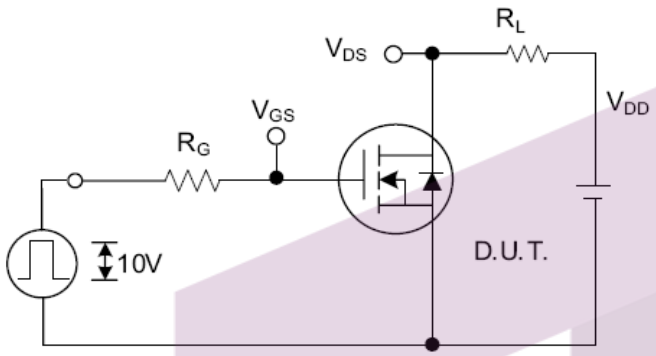


Fig. 2.1 Switching Test Circuit

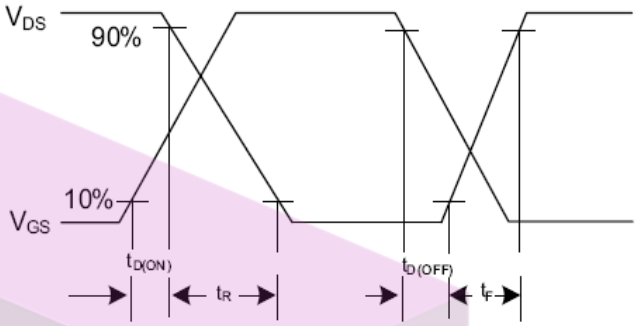


Fig. 2.2 Switching Waveforms

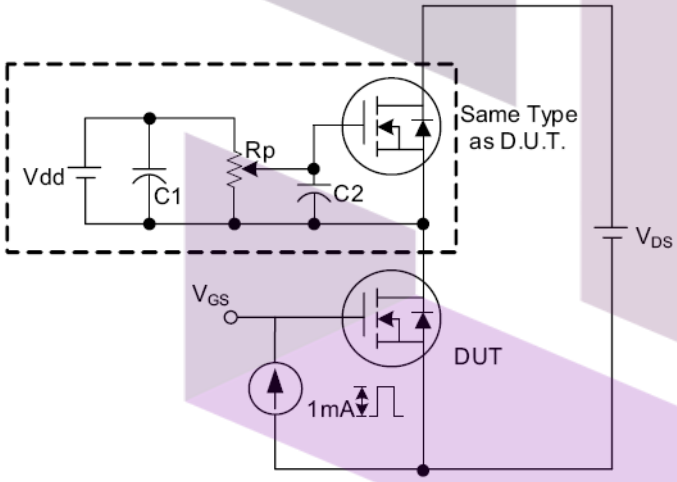


Fig. 3 . 1 Gate Charge Test Circuit

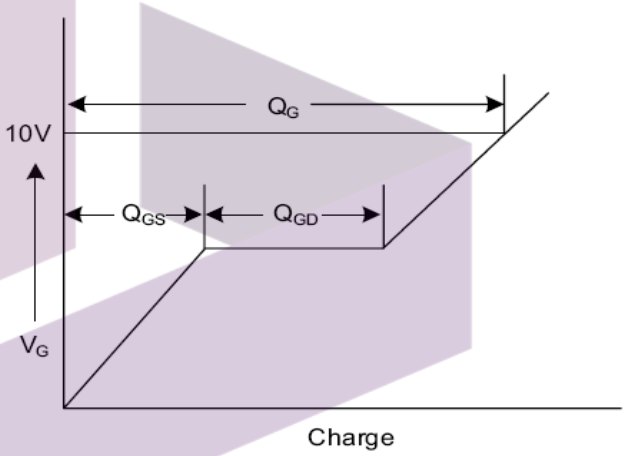


Fig. 3 . 2 Gate Charge Waveform

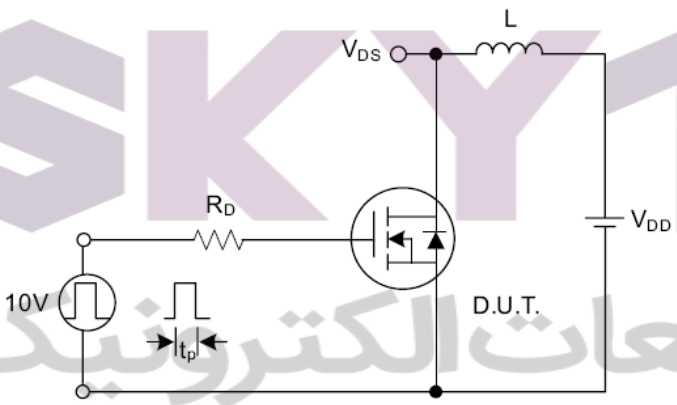


Fig. 4.1 Unclamped Inductive Switching Test Circuit

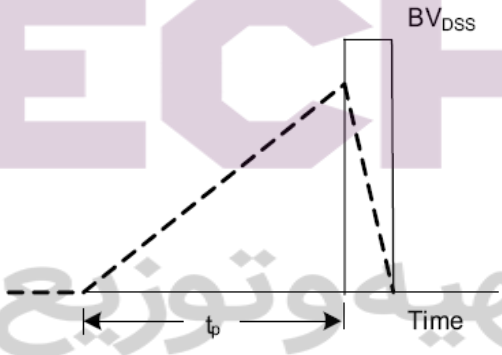


Fig. 4.2 Unclamped Inductive Switching Waveforms

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